Rev.E Mar.-2016

˜Yت

VRW0656 Ṃ Ṃ Ŀ QSQ Æ Ṁ ч s ǁ ˥ Silicon NPN transistor in a SOT-323 Plastic Package.

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S_F ᶻ /k_{IH} ᶻ ħ ⸗ ớ Ḅ /љ <348 Z Ӥ ´

High P_C and h_{FE}, excellent h_{FE} linearity, complementary pair with 9015W.

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Low frequency, low noise pre-amplifier.

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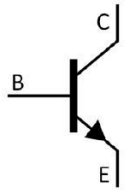

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PIN1 χ Emitter PIN 2 χ Base PIN 3 χ Collector

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h_{FE} Classifications Symbol	A	B	C	D
h_{FE} Range	60 150	100 300	200 600	400 1000
Marking	HJ6A	HJ6B	HJ6C	HJ6D

v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	Ш :ϒ Ţ Test Conditions	ώ ṇ Ö Min	Ɛ ʒ Ö Typ	ώ ² Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	5.0			V
Collector Cut-Off Current	I					

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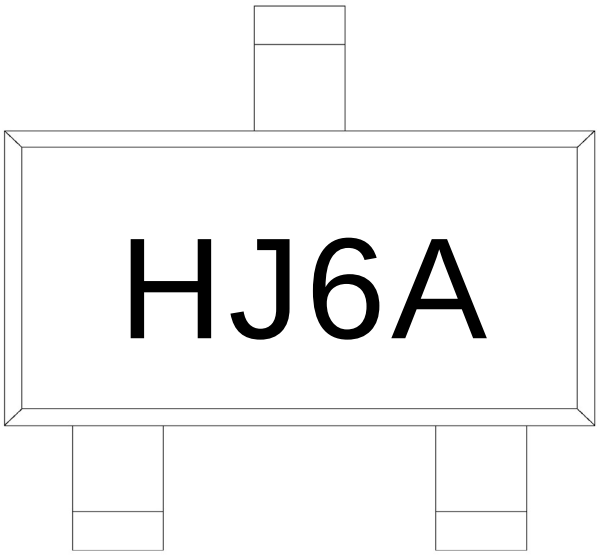

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K χ	ᴈ ᴝ ᴉ ᴓ
M9 χ	ᴈ ᴝ ᴺ ᴓ
D χ	ᴈ kᴉᴴ ᶜ ᶠ ᴓ

Note:

H:	Company Code.
J6:	Product Type.
A χ	h_{FE} Classifications Symbol

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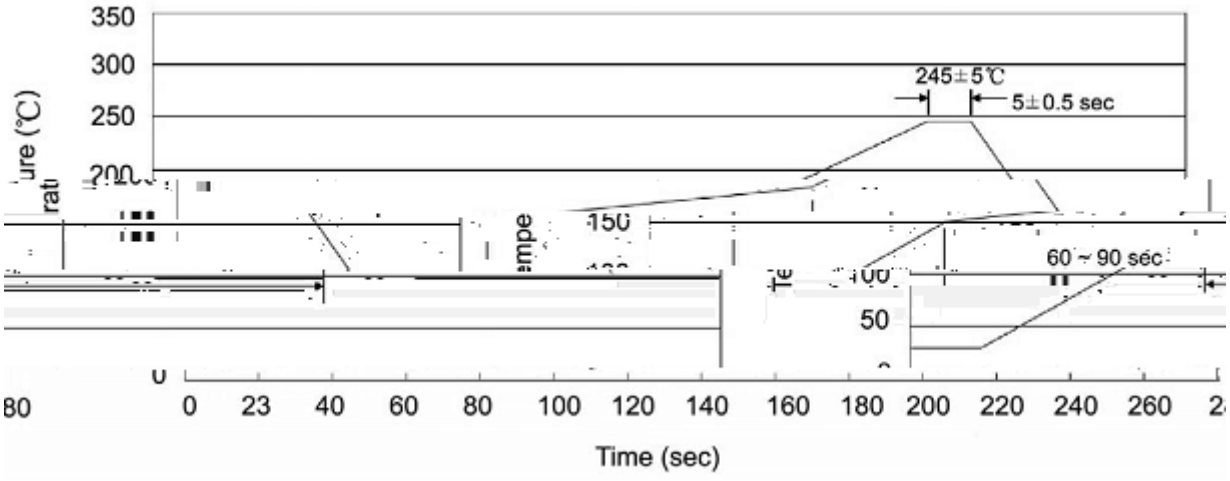

ب ˝ χ

1 ʃ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ɮ 60 Ḱ 90sec;

2 Š Ö □ ỷ 245 ° 5 ɬ ı `H ɮ ˋY ⅄ ⅉ 5 ° 0.5sec;

3 ì ˙ ⅂ ˛ ɔ ɯ ỷ ⅉ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:245 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

⅃ ü q ˝ `Y Ţ

□ ỷ χ 260 ° 5 ɬ `H ɮ χ 10 ° 1 sec. Temp.:260±5 Time:10±1 sec

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ɔ ` γ ⊢ / REEL

Package Type	Units					Dimension (unit mm³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 ×8	180×120×180	390×385×205

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